L Number	Hits	Search Text	DB	Time stamp
1	495266	dielectric insulat$3	USPAT; US-PGPUB	2002/09/07 19:26
2	87316	(dielectric insulat$3) and gate	USPAT; US-PGPUB	2002/09/07 19:26
3	16217	((dielectric insulat$3) and gate) and spacer	USPAT; US-PGPUB	2002/09/07 19:26
4	15506	(((dielectric insulat$3) and gate) and spacer) and (recess open$3 hole via contact trench)	USPAT; US-PGPUB	2002/09/07 19:33
6	1634	((((dielectric insulat$3) and gate) and spacer) and (recess open$3 hole via contact trench)) and (isotropic$5 near5 etch$3)	USPAT	2002/09/07 19:27
8	241	((((dielectric insulat$3) and gate) and spacer) and (recess open$3 hole via contact trench)) and (isotropic$5 near5 etch$3)	US-PGPUB	2002/09/07 19:20
9	946251	dielectric insulat$3	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:26
10	72774	(dielectric insulat$3) and gate	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:26
11	3911	((dielectric insulat$3) and gate) and spacer	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:26
12	2227	(((dielectric insulat$3) and gate) and spacer) and (recess open$3 hole via contact trench)	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:27
13	48	((((dielectric insulat$3) and gate) and spacer) and (recess open$3 hole via contact trench)) and (isotropic$5 near5 etch$3)	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:31
14	48244	(source drain) same junction	USPAT; US-PGPUB	2002/09/07 19:59
15	1526	((source drain) same junction) and ((silicon near5 germanium) SiGe)	USPAT; US-PGPUB	2002/09/07 19:59
16	1446	(((source drain) same junction) and ((silicon near5 germanium) SiGe)) and (recess open$3 hole via contact trench)	USPAT; US-PGPUB	2002/09/07 19:34
17	1278	(((source drain) same junction) and ((silicon near5 germanium) SiGe)) and (recess open$3 hole via contact trench)	USPAT	2002/09/07 19:59
18	14097	(source drain) same junction	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:59
19	425	"19" and ((silicon near5 germanium) SiGe)	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:59